



#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

#### **Features**

- Low On-Resistance: R<sub>DS(ON)</sub> < 88mΩ @ V<sub>GS</sub> = 4.5V R<sub>DS(ON)</sub> < 138mΩ @ V<sub>GS</sub> = 2.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42
  Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

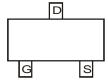


SOT323

Top View







Pin Configuration

# Ordering Information (Note 4)

	Part Number	Case	Packaging				
	DMN3150LW-7	SOT323	3000/Tape & Reel				
Notes:	es: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.						

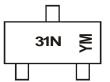
No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



31N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2008	~	20	16	2017	2018	2019	2020	20	21	2022	2023
Code	V	~	[	)	E	F	G	Н		I	J	K
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V <sub>DSS</sub>	28	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	$T_{A} = +25^{\circ}C$ $T_{A} = +70^{\circ}C$	ID	1.6 1.2	А
Drain Current (Note 5)	Pulsed	I <sub>DM</sub>	6.4	A
Body-Diode Continuous Current (Note 5)		Is	1.5	A

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	350	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{ heta}JA$	357	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

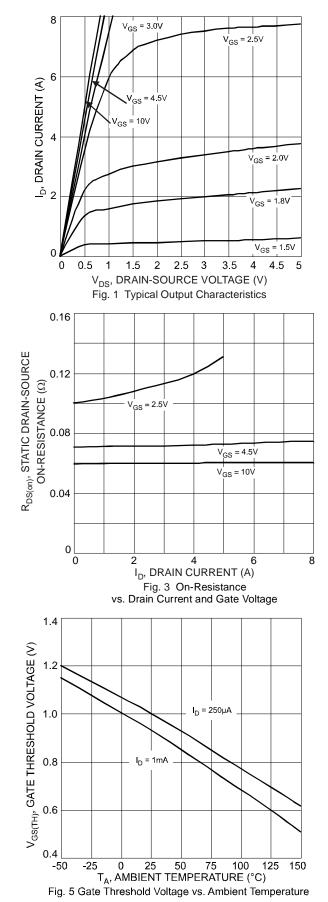
#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	28	_	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	800	nA	$V_{DS} = 28V, V_{GS} = 0V$	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±80 ±800	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 19V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.62	0.94	1.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		73 115	88 138	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1.6A V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1.2A	
Forward Transconductance	Y <sub>fs</sub>	_	5.4	_	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.7A	
Source-Drain Diode Forward Voltage	V <sub>SD</sub>			1.16	V	$V_{GS} = 0V, I_{S} = 1.5A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	305	—	pF		
Output Capacitance	C <sub>oss</sub>		74	_	pF	$V_{DS} = 5V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	48	_	pF		

Notes: 5. Device mounted on 1in<sup>2</sup> FR-4 PCB on 2oz. Copper. t ≤ 10 sec.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.



# **DMN3150LW**

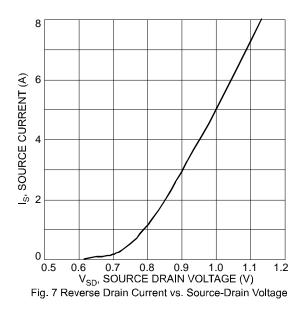


V<sub>DS</sub> = 5V Pulsed 6 I<sub>D</sub>, DRAIN CURRENT (A) 4 T<sub>A</sub> = 150°C 125°0 2 Т, = 85°C Τ<sub>Α</sub> -= 25°C T<sub>A</sub> = -5<sup>1</sup>5°C 0 0.5 2 1 1.5 2.5 3 V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Fig. 2 Typical Transfer Characteristics 1,000 f = 1MHz  $-T_{A} = 25^{\circ}C$ C, CAPACITANCE (pF) C<sub>iss</sub> 00 C<sub>oss</sub> C<sub>rss</sub> 10 0 5 10 15 20 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Fig. 4 Typical Total Capacitance 1.6 R<sub>DS(ON)</sub>, STATIC DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 1.4 V<sub>GS</sub> = 4.5V 1.2 I<sub>D</sub> = 1.6A 1.0 0.8 0.6 -25 25 50 75 100 125 150 -50 0 T<sub>A</sub>, AMBIENT TEMPERATURE (°C)

8

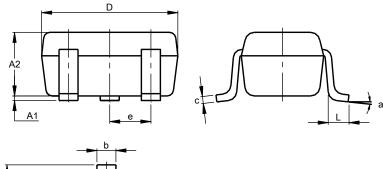
Fig. 6 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

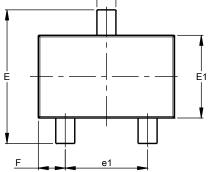




# Package Outline Dimensions

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.





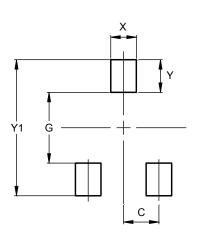
SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	8°						
All	All Dimensions in mm						

#### SOT323



### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	1.300		
Х	0.470		
Ŷ	0.600		
Y1	2.500		

#### **IMPORTANT NOTICE**

SOT323

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